

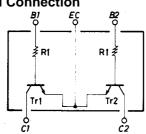
# **FC126**

NPN Epitaxial Planar Silicon Composite Transistor
Switching Applications
(with Bias Resistance)

#### **Features**

- · On-chip bias resistance (R1=47k $\Omega$ ).
- · Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC126 is formed with two chips, being equivalent to the 2SC3898, placed in one package.
- · Excellent in thermal equilibrium and pair capability.

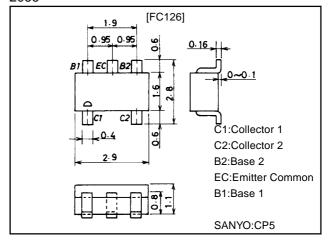
### **Electrical Connection**



## **Package Dimensions**

unit:mm

2066



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

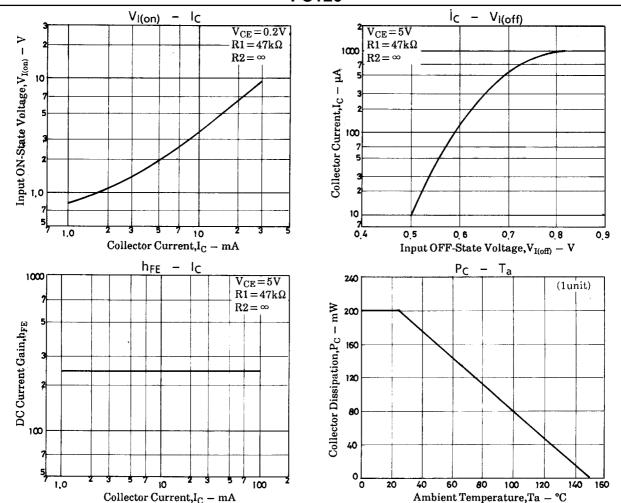
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		50	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		100	mA
Peak Collector Current	I <sub>CP</sub>		200	mA
Collector Dissipation	PC	1 unit	200	mW
Total Power Dissipation	PT		300	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	100			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA		250		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		3.3		pF
C-E Saturation Voltage	VCE(sat)	I <sub>C</sub> =5mA, I <sub>B</sub> =0.25mA		0.1	0.3	V
C-B Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	50			V
C-E Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =100μA, R <sub>BE</sub> =∞	50			V
Input OFF-State Voltage	V <sub>I(off)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.4	0.55	8.0	V
Input ON-State Voltage	V <sub>I(on)</sub>	V <sub>CE</sub> =0.2V, I <sub>C</sub> =5mA	0.8	2.0	4.0	V
Input Resistance	R1		33	47	61	kΩ

Note: The specifications shown above are for each individual transistor.

Marking:126



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